

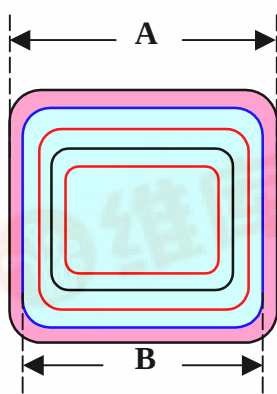


CMS-S040-040

SCHOTTKY BARRIER DIODE

Features :

- * Extremely low forward volts
- * Guard ring protection
- * Low reverse leakage current



Chip size(A): 1.016 * 1.016 mm²

Bond Pad size(B) : 0.889 * 0.889 mm²

Thickness : 300μm ± 20μm

Metalization : Anode Ti/Ni/Ag

Metalization : Cathode Ti/Ni/Ag

Electrical Characteristics	Sym.	Spec. Limit	Unit
Maximum Instantaneous Forward Volt at IF : 1.0Amp. 25°C	VF max	0.48	Volt
Minimum Instantaneous Reverse Voltage at IR : 200 uA 25°C	VR min.	43	Volt.
Minimum Non-repetitive Peak Surge current at 25°C	IFSM	40	Amp
Storage Temperature	TSTG	-65 to +125	°C

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